



STB35N60DM2 Information



For Reference Only

Part Number STB35N60DM2

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 28A

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STB35N60DM2 Specifications

Manufacturer Part Number STB35N60DM2 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series MDmesh? DM2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 14A, 10V		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesMDmesh? DM2FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs54nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2400pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)210W (Tc)	Manufacturer Part Number	STB35N60DM2
Package To-263-3, D2Pak (2 Leads + Tab), TO-263AB Series MDmesh? DM2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Manufacturer	STMicroelectronics
PackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesMDmesh? DM2FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs54nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2400pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)210W (Tc)	Category	Discrete Semiconductor Products
Series MDmesh? DM2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs54nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2400pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)210W (Tc)	Series	MDmesh? DM2
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 600V 28A (Tc) 28A (Tc) 10V 10V 250μA 54nC @ 10V 2400pF @ 100V 2400pF @ 100V 2400pF @ 100V 2400pF @ 100V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 28A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Current - Continuous Drain (Id) @ 25°C	28A (Tc)
Gate Charge (Qg) (Max) @ Vgs 54nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 2400pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 210W (Tc)	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) $\pm 25 \text{V}$ FET Feature-Power Dissipation (Max) 210W (Tc)	Gate Charge (Qg) (Max) @ Vgs	54nC @ 10V
FET Feature - Power Dissipation (Max) 210W (Tc)	Input Capacitance (Ciss) (Max) @ Vds	2400pF @ 100V
Power Dissipation (Max) 210W (Tc)	Vgs (Max)	±25V
-	FET Feature	-
Rds On (Max) @ Id, Vgs 110 mOhm @ 14A, 10V	Power Dissipation (Max)	210W (Tc)
	Rds On (Max) @ Id, Vgs	110 mOhm @ 14A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package D2PAK	Supplier Device Package	D2PAK
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Report errors?		Report errors?

STB35N60DM2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STB35N60DM2 Payment Methods



















STB35N60DM2 Shipping Methods













If you have any question about STB35N60DM2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com